iMiD 2022

The 22nd International Meeting on Information Display

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<tr><th>Exhibitor Introduction</th><td colspan="2">EngiOn has developed a technology that can be introduced into the actual process of predicting the electrical properties of IGZO itself. Vigth, created by Engion, can measure IV and CV characteristics directly after depositing IGZO thin film. We set up a system that can measure 3 terminals and developed a Microprobe unit that incorporated it into this technology.

This allows you to predict the Vth of IGZO and it is not an indirect method, so there is no need for a separate process. The application method is also infinite and can be used in various processes. It can be introduced throughout DISPLAY production line, can be used to evaluate properties without manufacturing devices in the R&D Lab, and is expected to be useful in developing IGZO deposition systems or metal oxide semiconductors of a new composition.
EngiOn is developing sixth-generation equipment with the goal in the second half of this year, and planning to develop large-scale automation</td></tr>
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	facilities that are more than 8th generation so that they can be applied to mass production processes. Also, we will proceed with additional sensitivity improvements for more precise measurements.
Exhibit Description	A new method and system to measure Metal-Oxide compound semiconductor (MOx) film have been developed. The new evaluation system can extract electrical characteristics of MOx-based TFT (Thin Film Transistor) such as carrier mobility and threshold voltage (V_TH) without additional patterned electrodes. The concept of the new method is similar to measuring 3-terminal-bottom gate TFT. This new method can provide in-situ monitoring data of MOx film to help yield improvement of MOx-based TFT applications.
Exhibit Product	**A New Evaluation System for Metal-Oxide Compound Semiconductor Film**